2o) in each case down to a recrystallization depth R that exceeds the surface roughness O of the bond surfaces (1o, 2o) with a bond temperature T_B that is greater than the recrystallization temperature.

8. Device in accordance with Claim 7, in which the cutting tool (5) can be adjusted in such a way that a second working is carried out at a speed v_o that exceeds the critical speed v_k, especially at a temperature T_o that is below the critical temperature T_k, in order to reduce the surface roughness O to less than 100 nm, preferably less than 10 nm, even more preferably less than 1 nm, and most preferably less than 0.1 nm.

9. Device in accordance with Claim 7, comprising a ~~C~~cutting tool (5) for working the first and/or second bond surfaces (1o, 2o) at a speed v_s that is below a critical speed v_k and at a temperature T_s that is above a critical temperature T_k and down to a surface roughness O of less than 1 μm.